

SPECIFICATION AMENDMENTS:

Please replace paragraph [0002] with the following amended paragraph:

--[0002]

BACKGROUND OF THE INVENTION

A conventional fuse circuit formed in a semiconductor device includes a conductive line and a pair of electrodes, connected to the ends of the conductive line. The conductive line includes a disconnection region, which is shaped to be narrower or thinner and is disconnected easily. The conductive line may be made of metal. In operation, a predetermined voltage is applied between the electrodes so that a predetermined current flows through the conductive line. When a specific increased amount of current flows through the conductive line, the disconnection region is will melt and become disconnected.--

Please replace paragraph [0009] with the following amended paragraph:

--[0009]

Fig. 1 is a block diagram illustrating the whole image of a semiconductor device according to a first preferred embodiment of the present invention. A semiconductor device 10 includes at least one fuse circuit 12 therein. The fuse circuit 12 may be a redundant fuse; a fuse used for adjusting a resistance and/or capacity; a fuse used for switching logic circuits in the semiconductor device 10; and a fuse used of adjusting an output level of signal. The present invention is applicable to ~~a variety~~ various kinds of semiconductor devices.--

Please replace paragraphs [0011] and [0012] with the following amended paragraphs:

--[0011]

From a plan view, the conductive line includes a first conductive region 16 and a second conductive region 18. As shown, the conductive regions form a bridge structure, with the second conductive region being suspended over the semiconductor substrate, i.e., with a space being formed therebetween. On the other hand, from a layered structure of view (cross-sectional view), the conductive line (16 & 18) includes first to thirds conductive layers 24, 26 and 28, and a passivation layer 22 as shown in Fig. 2B. The passivation layer 22 is not formed over the second conductive region 18. In the first conductive region 16, through holes 20 are formed in interlayer insulating layers. The second conductive region 18 ~~is formed on~~ includes the upper most layer 28.

[0012]

The first conductive region 16 has a multi-layered structure, as shown in Fig. 2B, in order to reduce the current density thereat. The second conductive region 18 has a single layer structure as shown in Fig. 2B, in order to increase the current density thereat. The second conductive region 18 may have a multi-layered structure, but should be less layered (i.e., have fewer layers) than the first conductive region 16. For instance, the first conductive region 16 ~~has~~ can have

more than ~~four~~ four-layered structure layers and the second conductive region 18 ~~has~~ may be a double-layered structure. According to the present invention, the second conductive region (disconnection region) 18 may be disconnected selectively and reliably, because electric current tends to be concentrated on the second conductive region 18. As a result, a fuse circuit can be designed small in size on a semiconductor substrate.--

Please replace paragraphs [0015] and [0016] with the following amended paragraphs:

--In operation, when a predetermined voltage is applied between the electrode pads 14a and 14b, electric current flows through the conductive line (16 & 18). When a predetermined amount of electric current flows through the second conductive region 18, the region 18 is ~~melt~~ melted and disconnected.

Fig. 5 is an explanatory diagram showing an arrangement of a fuse circuit according to a second preferred embodiment of the present invention. Fig. 5 corresponds to Fig. 4. The fuse circuit is of a laser trimming type. In other words, a laser beam is applied to the second conductive region 18 in order to disconnect it. The other structure and operation is almost the same as the first preferred embodiment, and the same description is not repeated to avoid redundancy. According to the second preferred embodiment, shown in Fig. 5, the second conductive regions 18 are arranged alternately, so that a laser beam can be

applied to a specific region 18 reliably. In other words, unnecessary regions are prevented from being disconnected accidentally. As a result, the conductive lines can be arranged with a smaller pitch or distance.--